FAIRCHILD SEMICONDUCTOR MPSA12 **NPN Darlington Transistor** • This device is designed for applications requiring extremely high current gain at currents to 1.0A. • Sourced from process 05. • See MPSA14 for characteristics.

TO-92 1. Emitter 2. Base 3. Collector MPSA12

Absolute Maximum Ratings * T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CES}	Collector-Emitter Voltage	20	V	
V _{CBO}	Collector-Base Voltage	20	V	
V _{EBO}	Emitter-Base Voltage	10	V	
I _C	Collector Current - Continuous	1.2	A	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C	

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_A=25°C unless otherwise noted

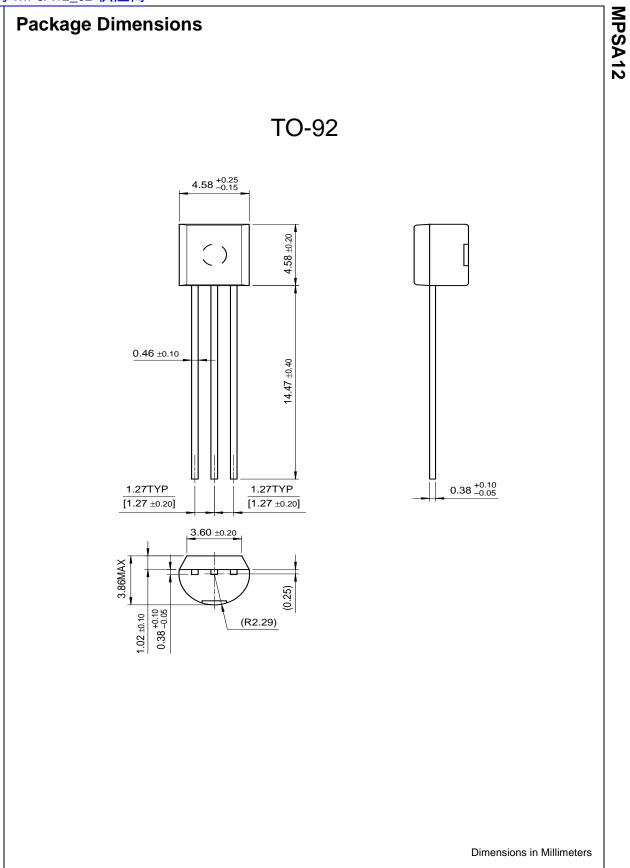
Parameter	Test Condition	Min.	Тур.	Max.	Units
cteristics					
Collector-Emitter Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm E} = 0$	20			V
Collector Cutoff Current	$V_{CB} = 15V, I_E = 0$			100	nA
Emitter Cutoff Current	$V_{CB} = 15V, I_{C} = 0$			100	nA
Emitter Cutoff Current	$V_{EB} = 10V, I_{C} = 0$			100	nA
cteristics *					
DC Current Gain	$V_{CE} = 5.0V, I_{C} = 10mA$	20,000			
Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0.01 {\rm mA}$			1.0	V
Base-Emitter On Voltage	I _C = 10mA, V _{CE} = 5.0V			1.4	V
	Collector-Emitter Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current Emitter Cutoff Current Emitter Cutoff Current cteristics * DC Current Gain Collector-Emitter Saturation Voltage	cteristicsCollector-Emitter Breakdown Voltage $I_C = 100\mu$ A, $I_E = 0$ Collector Cutoff Current $V_{CB} = 15$ V, $I_E = 0$ Emitter Cutoff Current $V_{CB} = 15$ V, $I_C = 0$ Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ Eteristics *DC Current GainDC Current Gain $V_{CE} = 5.0$ V, $I_C = 10$ mACollector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 0.01$ mA	cteristicsCollector-Emitter Breakdown Voltage $I_C = 100\mu$ A, $I_E = 0$ 20Collector Cutoff Current $V_{CB} = 15$ V, $I_E = 0$ 20Emitter Cutoff Current $V_{CB} = 15$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{CE} = 5.0$ V, $I_C = 10$ mA20,000Collector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 0.01$ mA20,000	cteristicsCollector-Emitter Breakdown Voltage $I_C = 100\mu$ A, $I_E = 0$ 20Collector Cutoff Current $V_{CB} = 15$ V, $I_E = 0$ 20Emitter Cutoff Current $V_{CB} = 15$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Current Gain $V_{CE} = 5.0$ V, $I_C = 10$ mA20,000Collector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 0.01$ mA20	cteristicsCollector-Emitter Breakdown Voltage $I_C = 100\mu$ A, $I_E = 0$ 20Collector Cutoff Current $V_{CB} = 15$ V, $I_E = 0$ 100Emitter Cutoff Current $V_{CB} = 15$ V, $I_C = 0$ 100Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 100Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 100Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 100Current Gain $V_{CE} = 5.0$ V, $I_C = 10$ mA20,000Collector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 0.01$ mA1.0

e Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%

Thermal Characteristics TA=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	625	mW
-	Derate above 25°C	5.0	mW/°C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient	200	°C/W

©2002 Fairchild Semiconductor Corporation



©2002 Fairchild Semiconductor Corporation

查询"MPSA12_02"供应商

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.